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**Ground state of double layer graphene heterostructures in the presence of charged impurities**<sup>1</sup> MARTIN RODRIGUEZ-VEGA, JONATHAN FISCHER, ENRICO ROSSI, College of William and Mary — A graphene double layer heterostructure is formed by two sheets of graphene separated by a thin dielectric film. Using the Thomas-Fermi-Dirac theory we have studied the carrier density profile in the presence of charged impurities. In this talk I will present our results for the case of heterostructures formed by two sheets of single-layer-graphene (SLG) and two sheets of bilayer-graphene (BLG). As for isolated layers, we find that the presence of charged impurities induces strong carrier density inhomogeneities, especially at low dopings where the density landscape breaks up in electron-hole puddles. We find that the amplitude of the carrier density inhomogeneities in double layers can be much lower than in isolated layers due to the better screening properties of double layer systems. I will then present results for the case of “hybrid” structures formed by one sheet of SLG and one sheet of BLG.

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